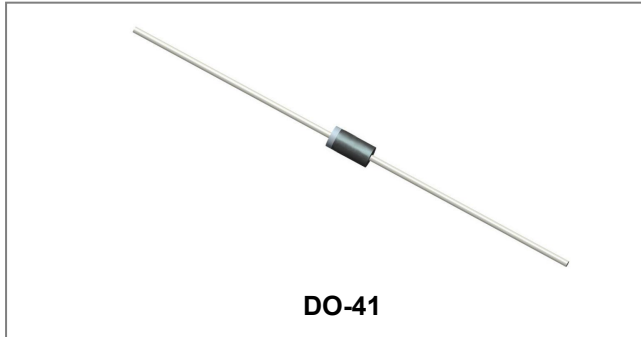


11DQ09/11DQ10 SCHOTTKY RECTIFIER



Features

- Low profile, axial leaded outline
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Very Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	90(11DQ09) 100(11DQ10)	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_L = 75^\circ\text{C}$, rectangular wave form On PC board 9mm ² island	1.1	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse, $T_C = 25^\circ\text{C}$	17	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 1 A, Pulse, $T_J = 25^\circ\text{C}$ @ 2 A, Pulse, $T_J = 25^\circ\text{C}$	0.76 -	0.85 0.96	V
	V_{F2}	@ 1 A, Pulse, $T_J = 125^\circ\text{C}$ @ 2 A, Pulse, $T_J = 125^\circ\text{C}$	0.60 -	0.68 0.78	V
Reverse Current*	I_{R1}	@ $V_R = \text{Rated } V_R$, Pulse, $T_J = 25^\circ\text{C}$	0.00002	0.5	mA
	I_{R2}	@ $V_R = \text{Rated } V_R$, Pulse, $T_J = 125^\circ\text{C}$	0.02	10	mA
Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	27	35	PF
Typical Series Inductance	L_S	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/ μs

* Pulse width < 300 μs , duty cycle < 2%

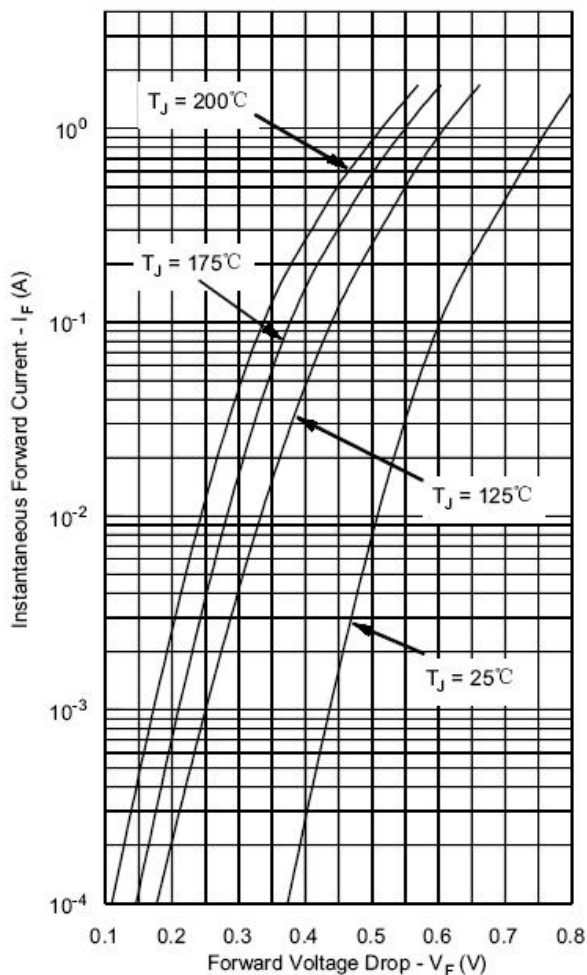
- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - sales@smc-diodes.com •

Thermal-Mechanical Specifications:

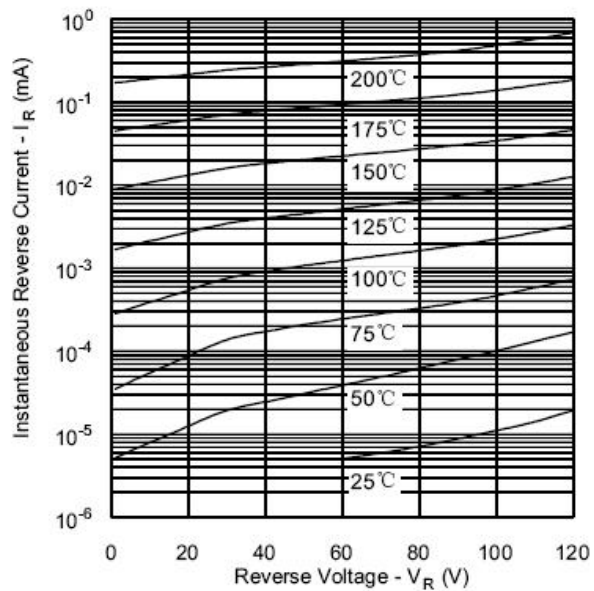
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-40 to +150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-	-40 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Ambient	$R_{\theta\text{JA}}$	-	100	$^{\circ}\text{C}/\text{W}$
Typical Thermal Resistance Junction to Lead	$R_{\theta\text{JL}}$	-	81	$^{\circ}\text{C}/\text{W}$
Approximate Weight	wt	-	0.34	g

Ratings and Characteristics Curves

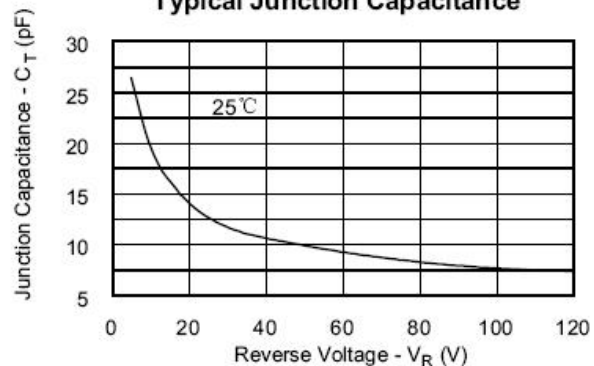
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



Mechanical Dimensions DO-41



SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	25.4	-	1.000	-
B	4.06	5.21	0.160	0.205
C	0.71	0.864	0.028	0.034
D	2.00	2.72	0.079	0.107

Ordering Information

Device	Package	Shipping
11DQ09 11DQ10	DO-41 (Pb-Free)	5000pcs /reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

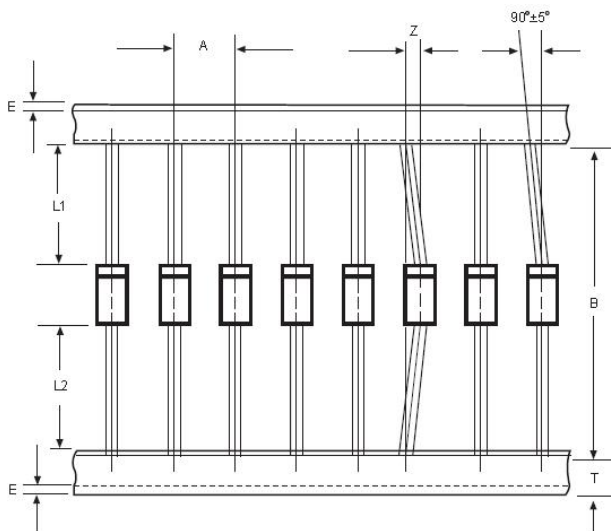


Where XXXXX is YYWWL

11DQ10 = Part Name
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape Specification DO-41



SYMBOL	Millimeters	
	Min.	Max.
A	4.50	5.50
B	50.9	53.9
Z	-	1.20
T	5.60	6.40
E	-	0.80
IL1-L2I	-	1.0

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